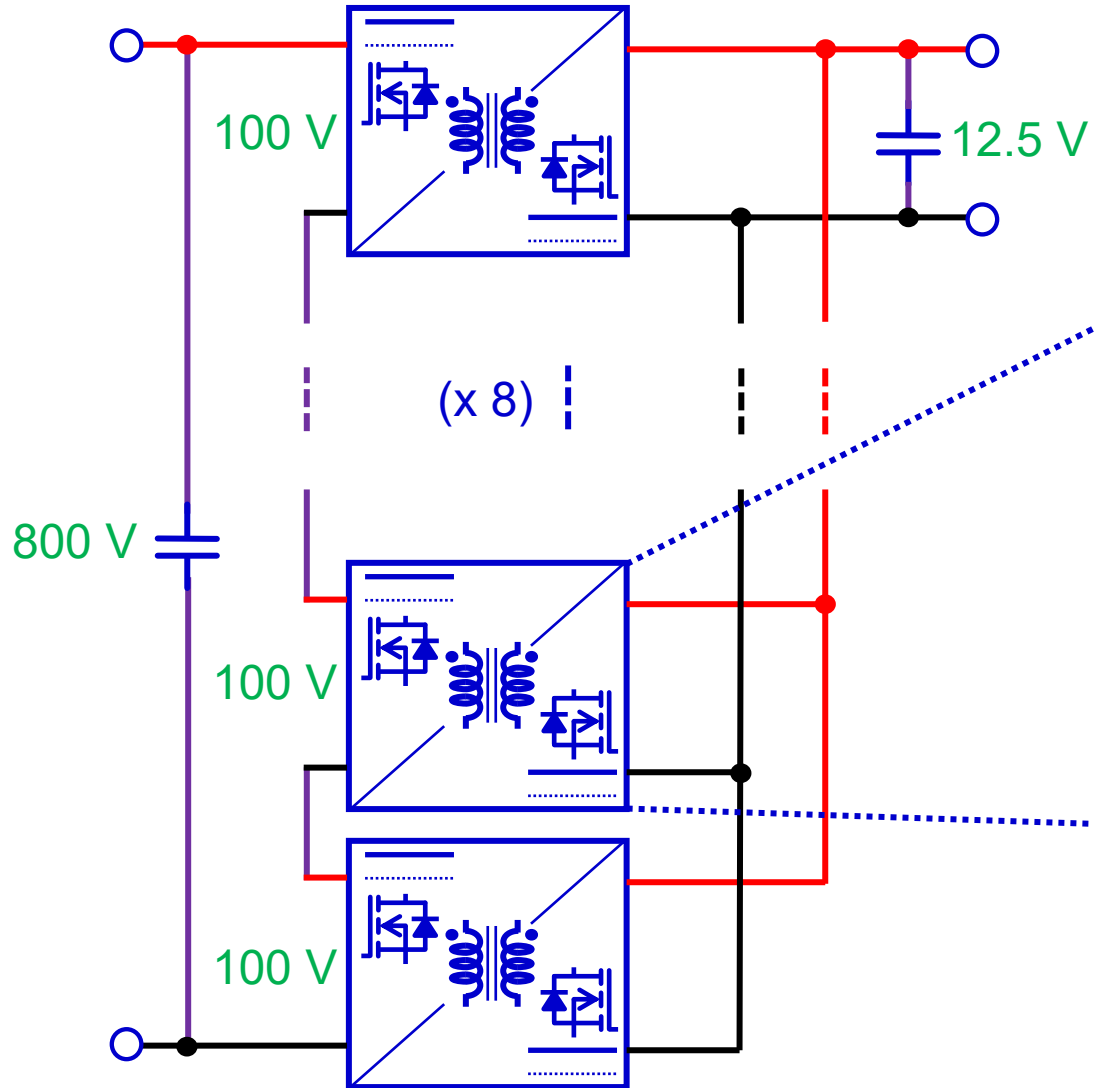


EPC91123KIT
800 V to 12.5 V
6 kW
May 2026



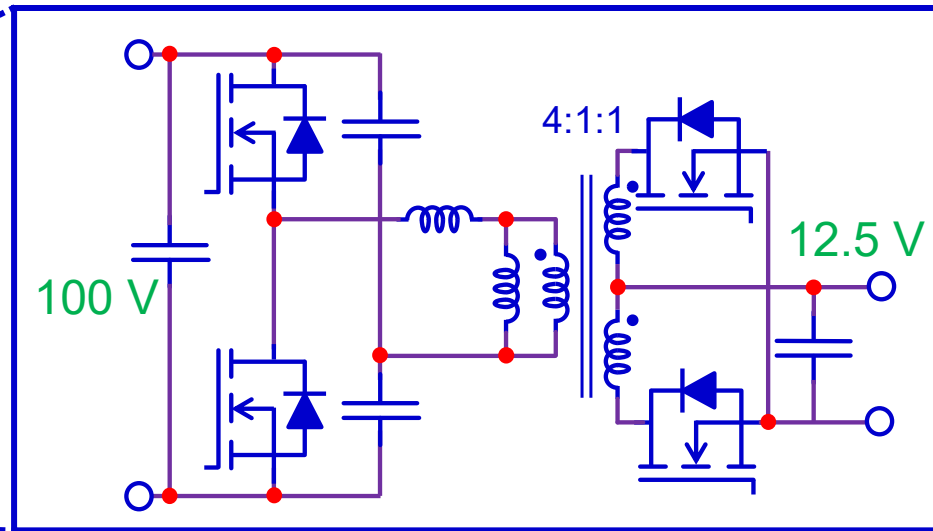
EFFICIENT POWER CONVERSION

EPC91123KIT Circuit Diagram



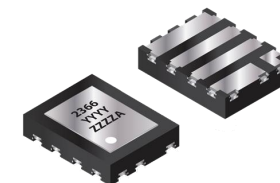
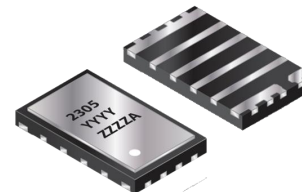
ISOP (Input-Series-Output-Parallel) of 8 LLC modules:

- Self Balancing
- Each LLC module: $V_{IN} = 100\text{ V}$ and $P_{OUT} = 750\text{ W}$



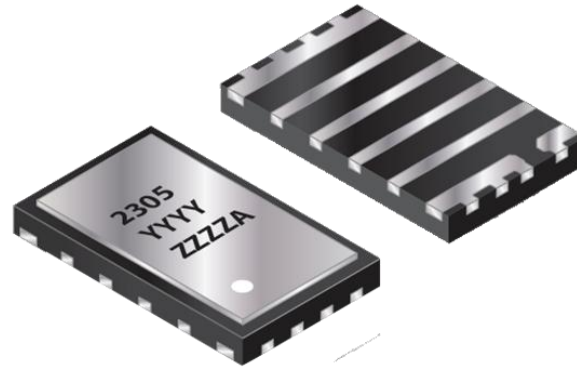
2 x EPC2305

4 x EPC2366

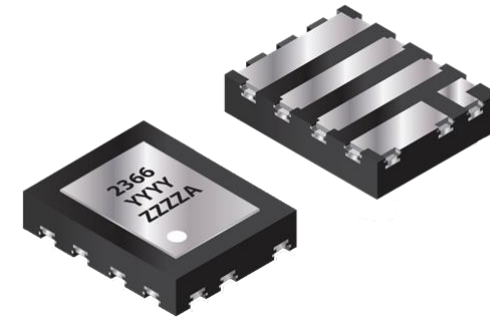


Featured GaN FETs

EPC2305



EPC2366



| | | |
|--|----------------------------|----------------------------|
| Package: QFN (double-sided cooling) | 3 mm x 5 mm | 2.6 mm x 3.3 mm |
| Voltage rating | 150 V | 40 V |
| Typical $R_{DS(on)}$ ($V_{GS} = 5$ V) | 2.2 m Ω | 0.84 m Ω |
| Gate Charge Q_G ($V_{GS} = 5$ V) | 22 nC | 15 nC |
| Output Charge Q_{OSS} | 122 nC ($V_{DS} = 100$ V) | 18 nC ($V_{DS} = 12.5$ V) |
| Reverse Recovery Q_{RR} | 0 nC | 0 nC |

Benefits of the ISOP Topology

1. Superior GaN devices in primary side:
 - 150 V-GaN → better FOM and smaller size than 650 V-GaN
2. Simpler transformer design. For 800 V to 12.5 V, 6 kW:
 - ISOP with 650 V-GaN: 16:1:1, 3 kW transformer
 - ISOP with 150 V-GaN: 4:1:1, 750 W transformer
3. Fewer bus capacitors with interleaving LLC modules
4. Distributed losses on primary side devices → no hotspots
5. Lower EMI
6. Ideal topology for high step-down ratio (800 V to 12 V or 6 V)

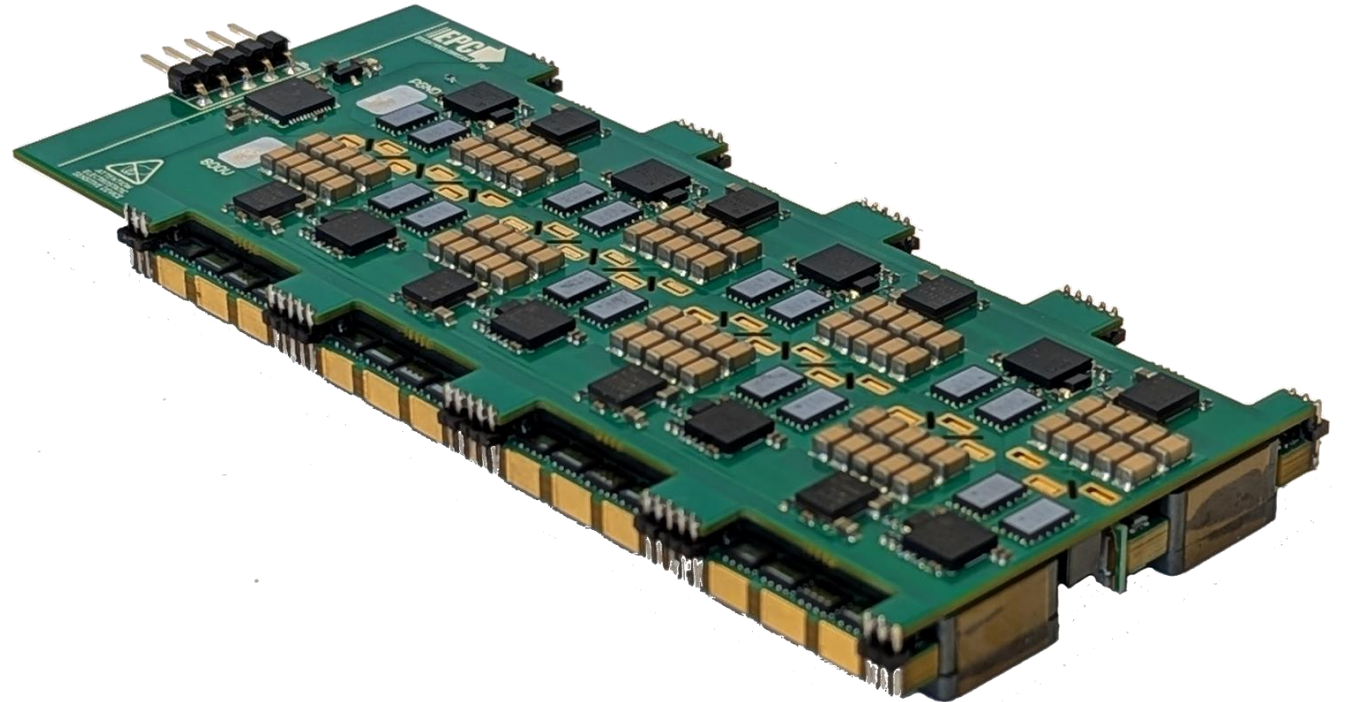
Converter Specifications

Converter details:

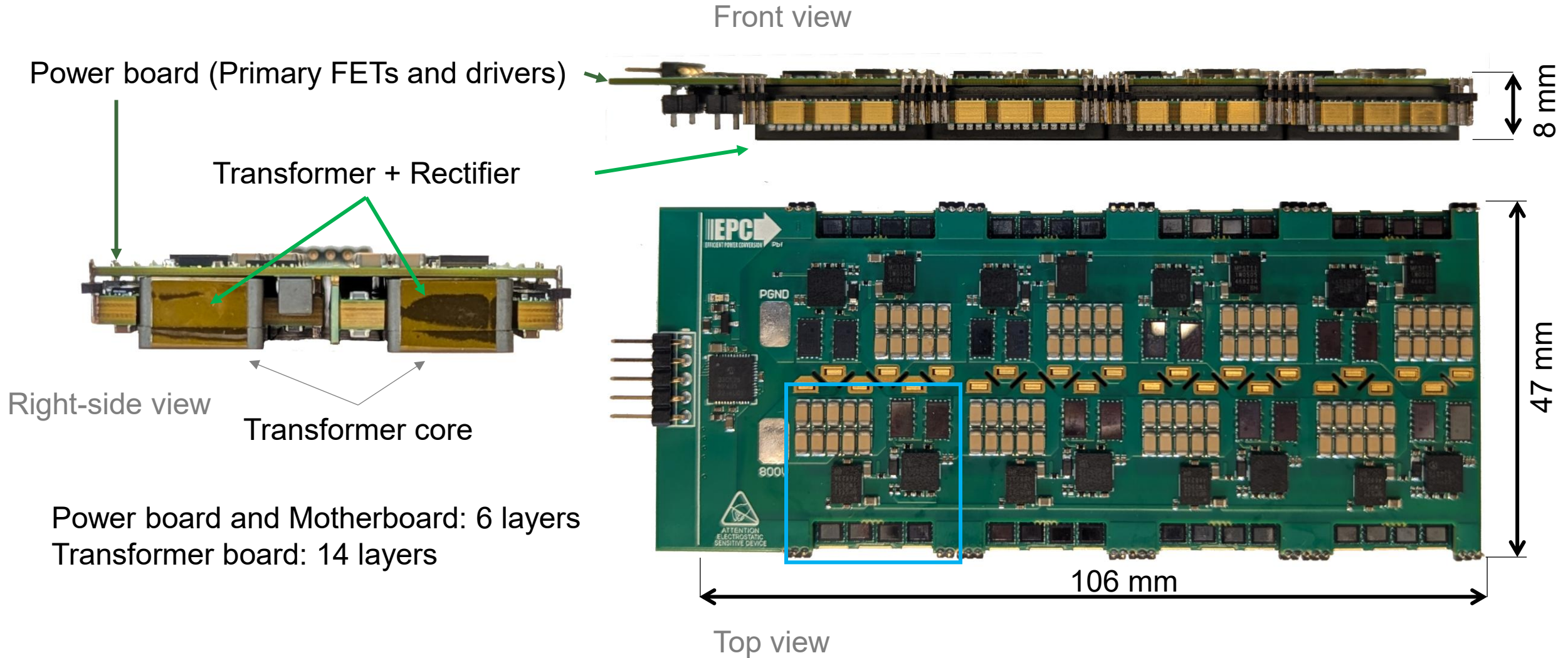
- Voltage ratio: 800 V to 12.5 V (fixed)
- $P_{OUT} = 6 \text{ kW}$
- Area: 4982 mm² (830 mm²/kW)
- Height: 8 mm

LLC module details:

- 100 V to 12.5 V, 750 W
- Primary: Half-bridge using EPC2305
- Center-tap rectifier using 2 x EPC2366
- Resonant frequency ~ 1 MHz

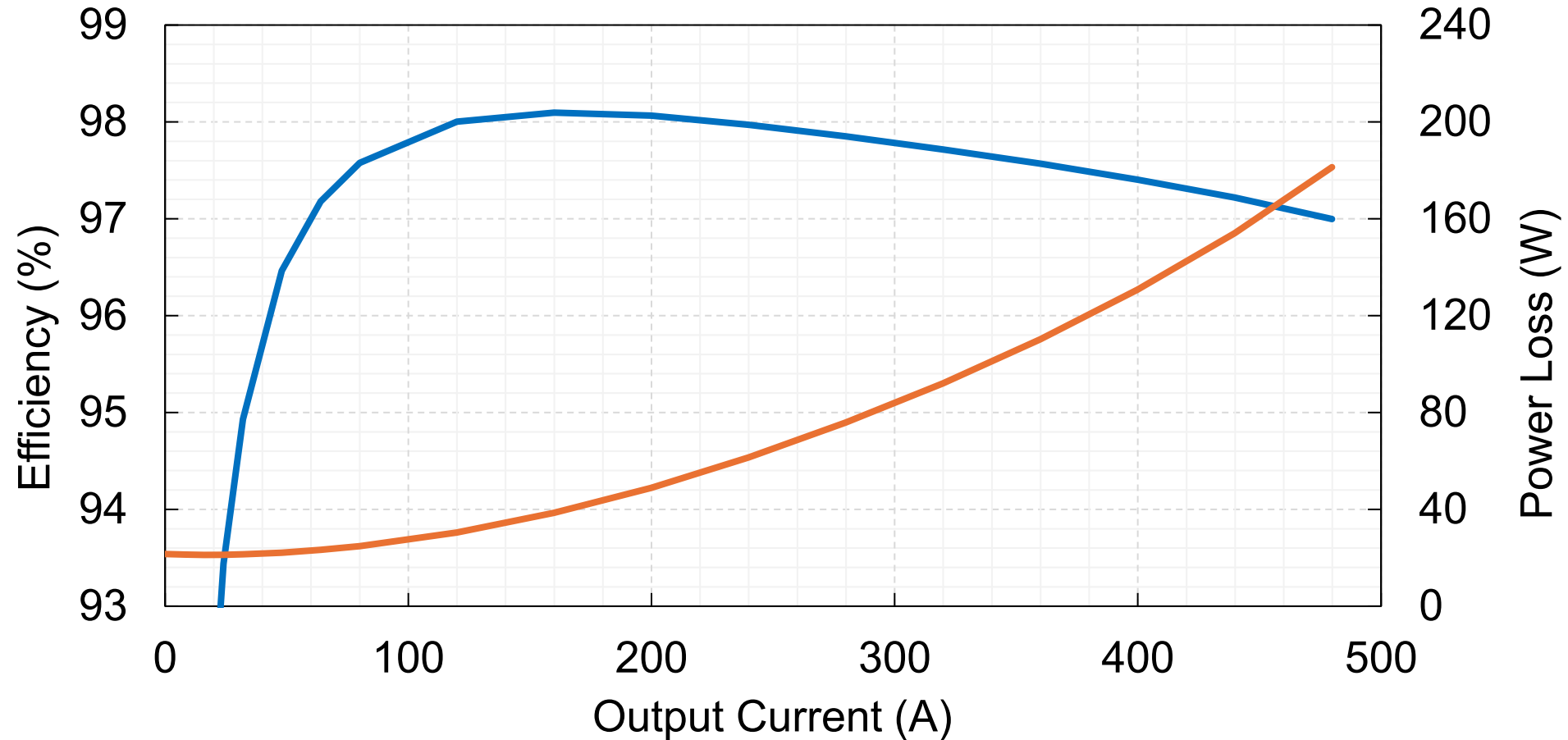


Converter Construction



Power board and Motherboard: 6 layers
Transformer board: 14 layers

Converter Performance



Additional ~7.5 W of housekeeping power (~1.45 A @ 5V) for the ISOP converter, (~0.94 W per module)

Bill of Materials



Key components:

| Component | Part Number | Description | Quantity | |
|--------------------------|------------------------|--|----------|-------|
| | | | Per LLC | Total |
| Primary FETs | EPC2305 | 150V GaN FETs, 2.2m Ω , 3x5 QFN | 2 | 16 |
| Secondary FETs | EPC2366 | 40V GaN FETs, 0.84m Ω , 2.6x3.3 QFN | 4 | 32 |
| Primary Gate Driver | MP18831-4A | Isolated Gate Drive 2-ch | 1 | 8 |
| Secondary Gate Driver | LMG1020 | Low-Side Gate Driver | 2 | 16 |
| Transformer Core | Proterial ER23/7.2/13* | ML95S material, size ER23/7.2/13* | 2 | 16 |
| Isolated 5V Power Supply | MIE1W0505BGLVH | 5V/5V 1W Isolated DC-DC | 1 | 8 |
| Isolators | ISO7740DWR | Dig. Isolator 4-ch | - | 2 |
| Controller | DSPIC33CK256MP605 | 100MHz 16-bit Microcontroller | - | 1 |

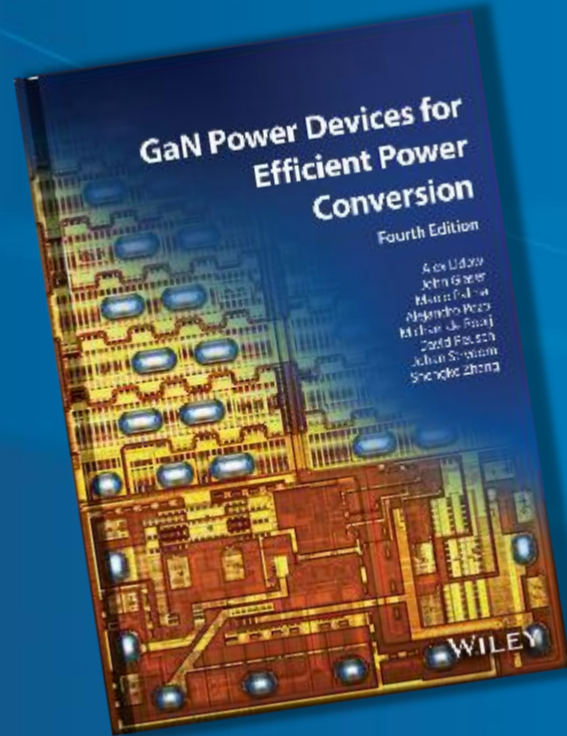


Click on images to learn more

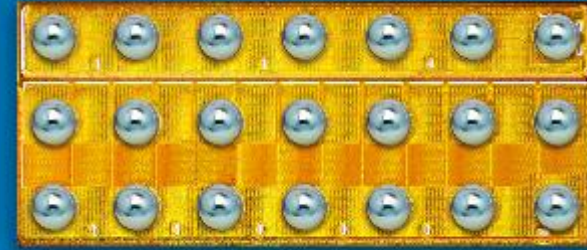


How To GaN Video Series

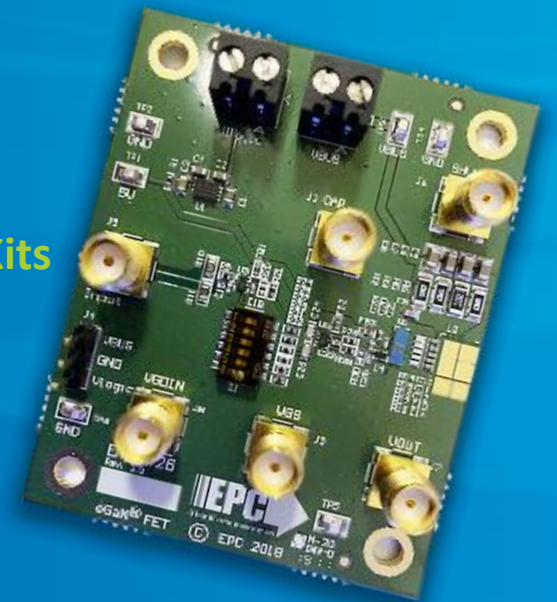
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